

IN THE ABSTRACT

Please add the following Abstract of the Disclosure on a new page after the claims of this application:

--SEMICONDUCTING DEVICES AND METHOD OF MAKING THEREOF

ABSTRACT OF THE DISCLOSURE

The invention relates to a process for providing a semiconducting device including the steps of depositing a semiconducting layer onto a substrate by means of heating a gas to a predetermined, disassociation temperature so that the gas dissociates into fractions, whereby these fractions subsequently condense on the substrate to build up a semiconducting layer.--

REMARKS

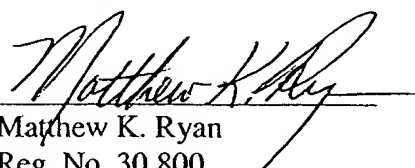
Please enter this Supplemental Preliminary Amendment in the file of this application. By this Supplemental Preliminary Amendment, an Abstract of the Disclosure has been added for this application and a copy of the Declaration and Power of Attorney as filed in the parent application (Serial No. 09/331,528) is attached.

Attached hereto is a marked-up version of the changes made to the application by the current amendment. The attached page is captioned "Version with markings to show changes made."

Please charge any additional fees incurred by reason of this response and not paid herewith to Deposit Account No. 50-0320.

Respectfully submitted,
FROMMER LAWRENCE & HAUG LLP
Attorneys for Applicants

By:


Matthew K. Ryan
Reg. No. 30,800
(212) 588-0800

"VERSION WITH MARKINGS TO SHOW CHANGES MADE."

The following Abstract of the Disclosure has been added on a new page after the claims of this application:

--SEMICONDUCTING DEVICES AND METHOD OF MAKING THEREOF

ABSTRACT OF THE DISCLOSURE

The invention relates to a process for providing a semiconducting device including the steps of depositing a semiconducting layer onto a substrate by means of heating a gas to a predetermined, disassociation temperature so that the gas dissociates into fractions, whereby these fractions subsequently condense on the substrate to build up a semiconducting layer. --